

Vishay Semiconductors



Small Signal Schottky Diode

Features

- These diodes feature very low turn-on voltage and fast switching
 These devices are protected by a PN (e3)
- These devices are protected by a PN junction guard ring against excessive voltage, such as electrostatic discharges
- · Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



Mechanical Data

Case: SOD123 Plastic case Weight: approx. 10.3 mg Packaging Codes/Options: GS18/10 k per 13" reel (8 mm tape), 10 k/box GS08/3 k per 7" reel (8 mm tape), 15 k/box

Parts Table

Part	Ordering code	Type Marking	Remarks
BAT54W-V	BAT54W-V-GS18 or BAT54W-V-GS08	L4	Tape and Reel

Absolute Maximum Ratings

T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Repetitive peak reverse voltage		V _{RRM}	30	V
Forward continuous current	T _{amb} = 25 °C	١ _F	200 ¹⁾	mA
Repetitive peak forward current	t_p < 1 s, δ < 0.5, T_{amb} = 25 °C	I _{FRM}	300 ¹⁾	mA
Surge forward current	t_p < 10 ms, T_{amb} = 25 °C	I _{FSM}	600 ¹⁾	mA
Power dissipation ¹⁾	$T_{amb} = 25 \ ^{\circ}C$	P _{tot}	150 ¹⁾	mW

¹⁾ Valid provided that electrodes are kept at ambient temperature

Thermal Characteristics

 $T_{amb} = 25 \ ^{\circ}C$, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Thermal resistance junction to ambient air		R _{thJA}	650 ¹⁾	K/W
Maximum junction temperature		Тj	125	°C
Storage temperature range		T _{stg}	- 65 to + 150	°C

¹⁾ Valid provided that electrodes are kept at ambient temperature

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Electrical Characteristics

 $T_{amb} = 25 \ ^{\circ}C$, unless otherwise specified

Parameter	Test condition	Symbol	Min	Тур.	Max	Unit
Reverse breakdown voltage	tested with 100 µA pulses	V _(BR)	30			V
Leakage current ²⁾	V _R = 25 V	I _R			2	μA
Forward voltage ²⁾	I _F = 0.1 mA	V _F			240	mV
	I _F = 1 mA	V _F			320	mV
	I _F = 10 mA	V _F			400	mV
	I _F = 30 mA	V _F			500	mV
	I _F = 100 mA	V _F			800	mV
Diode capacitance	V _R = 1 V, f = 1 MHz	CD			10	pF
Reverse recovery time	$I_{F} = I_{R} = 10 \text{ mA}; I_{R} = 1 \text{ mA}; R_{L} = 100 \Omega$	t _{rr}			5	ns

 $^{2)}$ Pulse test: tp < 300 µs, θ < 2 %

Typical Characteristics

 T_{amb} = 25 °C, unless otherwise specified

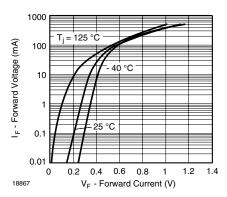


Figure 1. Typical Forward Voltage Forward Current at Various Temperatures

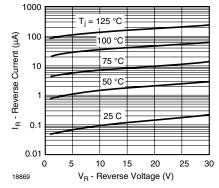


Figure 3. Typical Variation of Reverse Current at Various Temperatures

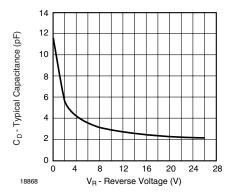


Figure 2. Typical Capacitance °C vs. Reverse Applied Voltage V_R

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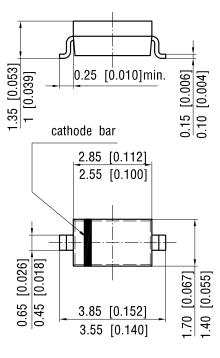
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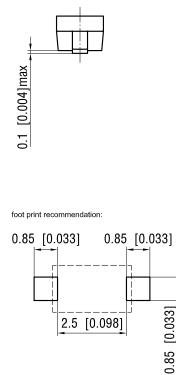


BAT54W-V

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Package Dimensions in mm (Inches)





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Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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